

ALIGNMENT SYSTEM AND METHOD USING BRIGHT SPOT
AND BOX STRUCTURE

ABSTRACT OF THE DISCLOSURE

5 There is provided a method for measuring planarized
features on a wafer of a semiconductor device. The
planarized features on the wafer are illuminated. A
reflected light beam with respect to the planarized
features is detected. Optical characteristics of the
10 reflected light beam are analyzed to determine information
corresponding to the planarized features. Preferably, the
analyzing step maximizes an analysis of the optical
characteristics based upon a simplified geometry of the
planarized features with respect to a geometry of similar,
15 un-planarized features. Moreover, preferably, the
analyzing step maximizes an analysis of the optical
characteristics based upon a reduction in complexity of the
planarized features due to a similarity in refractive
indexes corresponding to a bulk silicon substrate and a
20 poly silicon fill of the semiconductor device.